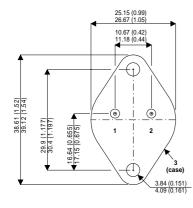
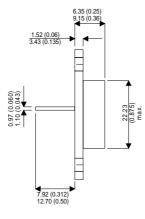


MECHANICAL DATA Dimensions in mm(inches)





TO-3(TO204AA)

PIN 1 — Base PIN 2 — Emitter

Case is Collector

NPN MULTI - EPITAXIAL POWER TRANSISTOR

FEATURES

- HIGH VOLTAGE
- LOW SATURATION VOLTAGES
- HIGH RELIABILITY

APPLICATIONS

- POWER SWITCHING CIRCUITS
- LINEAR APPLICATIONS

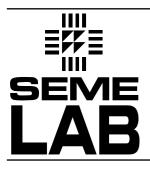
ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V _{CBO}	Collector – Base Voltage (I _E = 0)	60V
V _{CEO}	Collector – Emitter Voltage $(I_B = 0)$	60V
V_{EBO}	Emitter – Base Voltage $(I_{C} = 0)$	5V
I _C	Collector Current	25A
I _{CM}	Peak Collector Current	50A
I _B	Base Current	7.5A
P _{tot}	Total Power Dissipation at $T_{case} \le 25^{\circ}C$	200W
T _{stg} ,	Storage Temperature	–65 to 200°C
т _ј	Junction Temperature	200°C

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	ector - Emitter Breakdown		Min.	Тур.	Max.	Unit V
V _{CEO(BR)*}	Collector - Emitter Breakdown Voltage			60			
$V_{BE^{\star}}$	Base – Emitter Voltage	I _C = 10A	$V_{CE} = 4V$			1.5	V
I _{CEV}	Collector Cut-off Current	V _{CE} = 60V	$V_{BE} = -1.5V$			1.0	– mA
			T _{CASE} =150°C			10	
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5V	I _C = 0			1.0	mA
I _{CEO}	Collector Cut-off Current	V _{CE} = 30V	$I_{B} = 0$			2	mA
I _{CBO}	Collector Cut-off Current	V _{CE} = 60V	$I_E = 0$			1.0	mA
V _{CE(sat)*}	Collector – Emitter Saturation	I _C = 15A	I _B = 1.5A			1.0	V
	Voltage	I _C = 25A	I _B = 6.25A			4	
V _{BE(sat)*}	Base – Emitter Saturation Voltage	I _C = 25A	I _B = 6.25A			2.5	V
h _{FE*}	DC Current Gain	I _C = 3A	$V_{CE} = 4V$	35			
		I _C = 10A	$V_{CE} = 4V$	20		100	
		I _C = 25A	$V_{CE} = 4V$	4			
h _{fe}	Small Signal Current Gain	$I_{C} = 3A$ $V_{CE} = 4V$	f = 1 KHz	20			—
C _{cbo}	Collector Base Capacitance	$I_E = 0$ $V_{CB} = 10V$	f = 1 MHz			500	pF
f _T	Transition Frequency	I _C = 1.0A V _{CB} = 10V	f = 1 MHz	4			MHz
t _r	Rise Time	$V_{CC} = 30V$ $I_{B1} = -I_{B2} = 1.0A$	I _C = 10A			0.7	
t _s	Storage Time					1.0	μs
t _f	Fall Time		-			0.8	

THERMAL CHARACTERISTICS

$R_{\theta JC}$ Thermal Resistance Junction to Case	Max	0.875	°C/W
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* Pulse test t_p = 300 μs , δ = 1.5 %

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